

Description

The VST10N030 uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

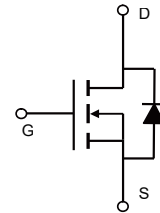
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

- $V_{DS} = 100V, I_D = 135A$
 $R_{DS(ON)} = 3.45m\Omega$ (Typ.) @ $V_{GS} = 10V$
- Excellent gate charge x $R_{DS(ON)}$ product(FOM)
- Very low on-resistance $R_{DS(ON)}$
- 150 °C operating temperature
- Pb-free lead plating



DFN5x6



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VST10N030	VST10N030-D56	DFN5x6	Ø330mm	12 mm	5000 units

Absolute Maximum Ratings (T_c=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	135	A
Drain Current-Continuous(T _c =100°C)	$I_D(100^\circ C)$	108	A
Pulsed Drain Current ^(Note 1)	I_{DM}	540	A
Maximum Power Dissipation	P_D	170	W
Derating factor		1.36	W/°C
Single pulse avalanche energy ^(Note 5)	E_{AS}	750	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	0.74	°C/W
--	-----------------	------	------

Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =67.5A	-	3.45	3.8	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =67.5A		130	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, F=1.0MHz	-	6300	-	PF
Output Capacitance	C _{oss}		-	560	-	PF
Reverse Transfer Capacitance	C _{rss}		-	40	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =50V, I _D =67.5A, V _{GS} =10V, R _G =3Ω	-	23	-	nS
Turn-on Rise Time	t _r		-	15	-	nS
Turn-Off Delay Time	t _{d(off)}		-	48	-	nS
Turn-Off Fall Time	t _f		-	16	-	nS
Total Gate Charge	Q _g	V _{DS} =50V, I _D =67.5A, V _{GS} =10V	-	110	-	nC
Gate-Source Charge	Q _{gs}		-	33		nC
Gate-Drain Charge	Q _{gd}		-	30		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =67.5A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	135	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =67.5A	-	70	-	nS
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs (Note3)	-	117	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : T_J=25°C, V_{DD}=50V, V_G=10V, L=0.5mH, R_G=25Ω

Typical Electrical and Thermal Characteristics

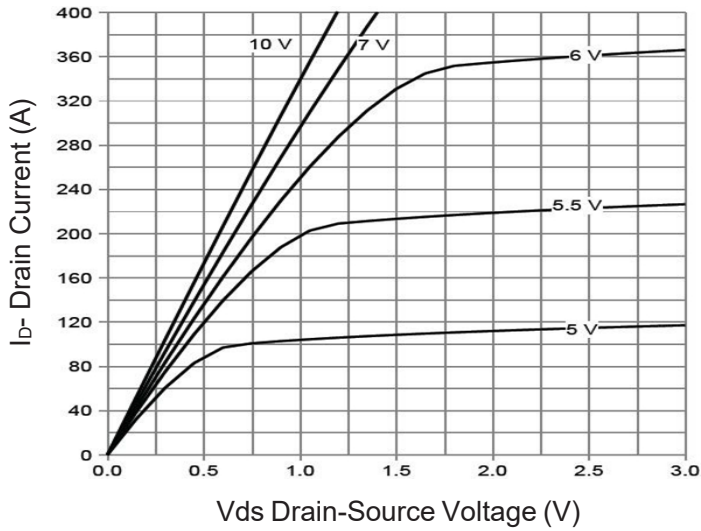


Figure 1 Output Characteristics

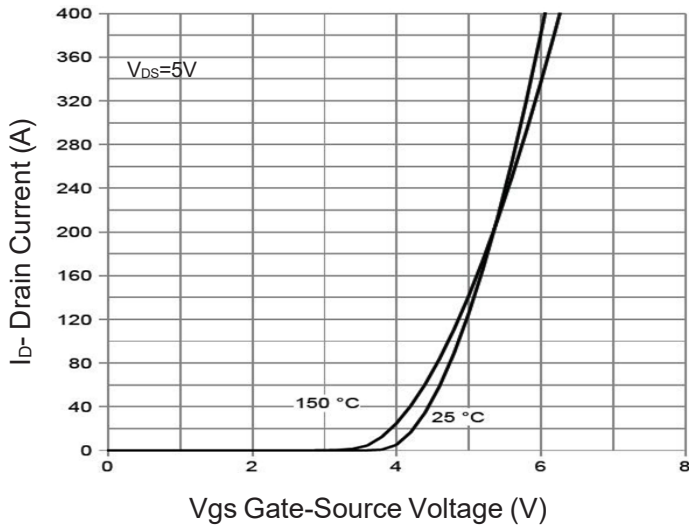


Figure 2 Transfer Characteristics

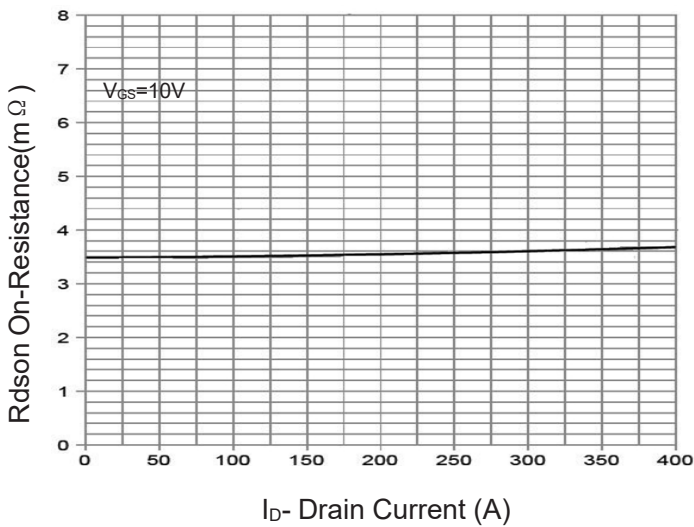


Figure 3 Rdson- Drain Current

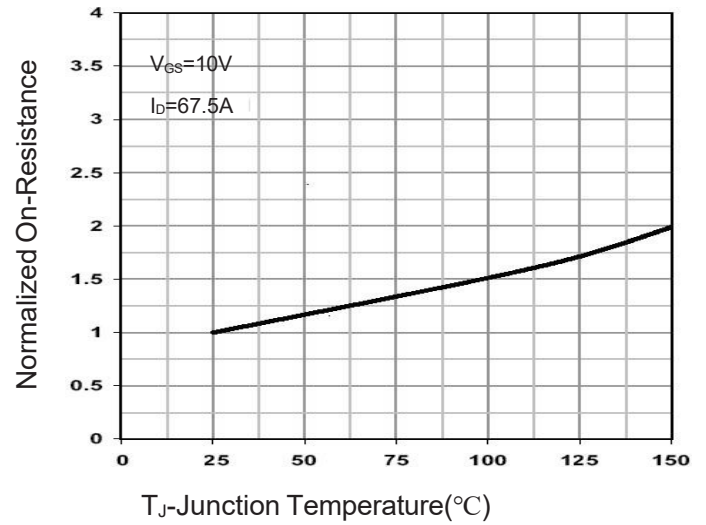


Figure 4 Rdson-Junction Temperature

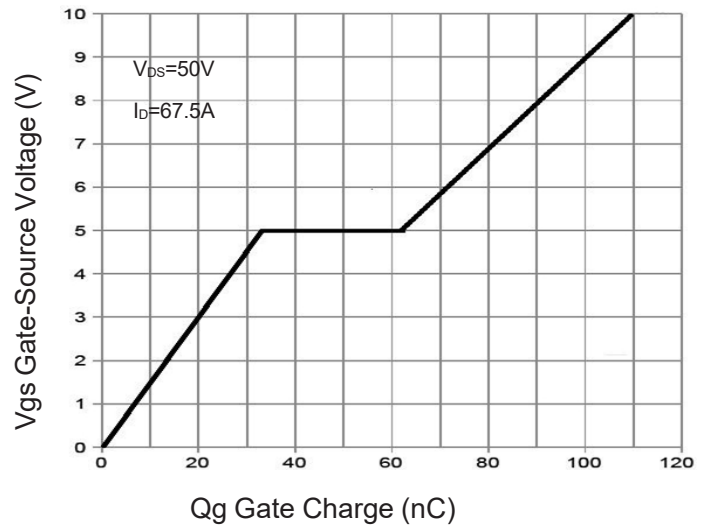


Figure 5 Gate Charge

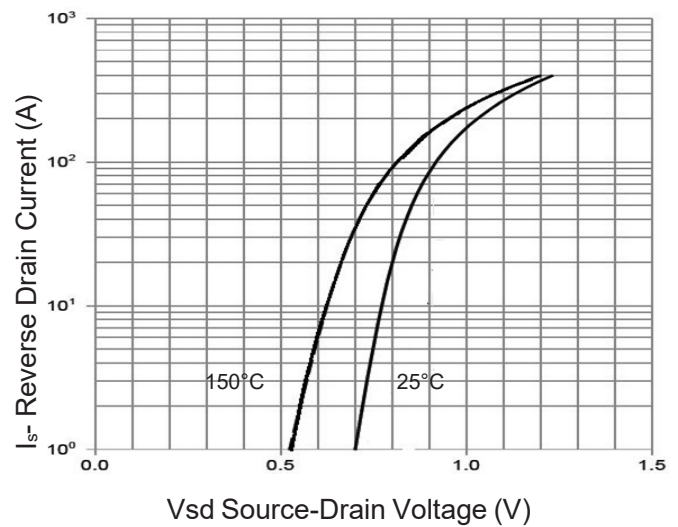
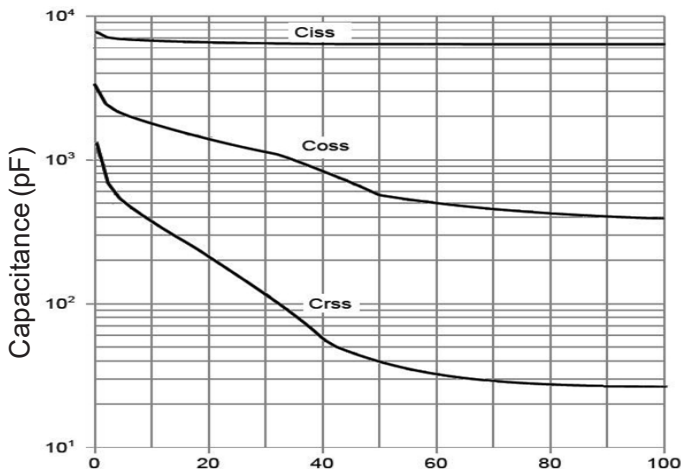
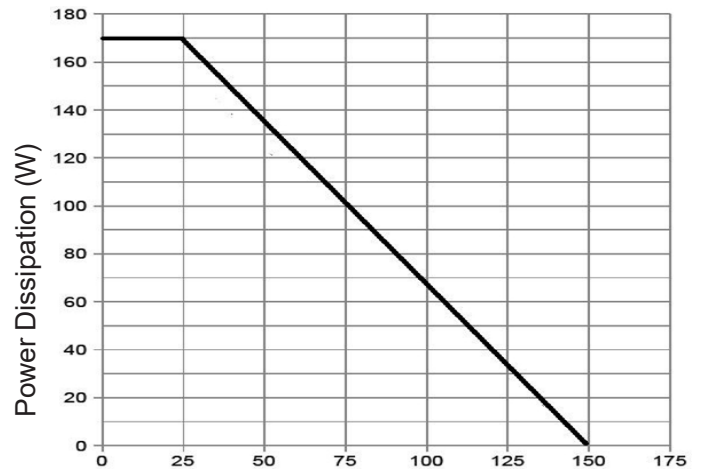


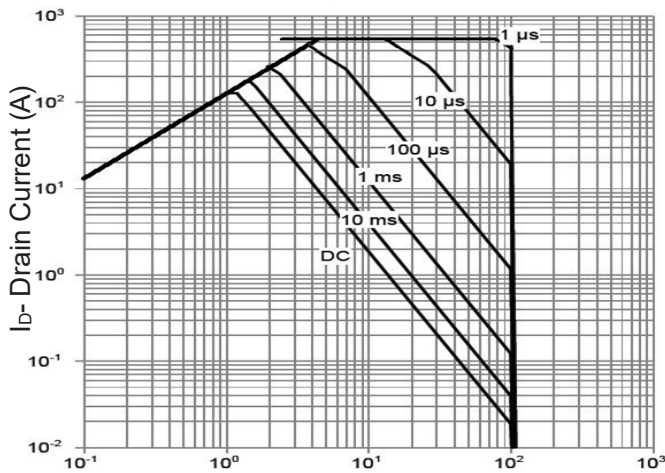
Figure 6 Source- Drain Diode Forward



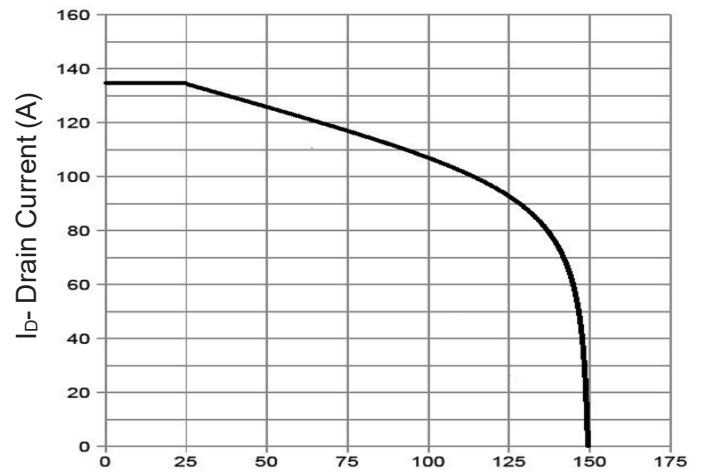
Vds Drain-Source Voltage (V)
Figure 7 Capacitance vs Vds



T_J-Junction Temperature(°C)
Figure 9 Power De-rating



Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area



T_J-Junction Temperature (°C)
Figure 10 Current De-rating

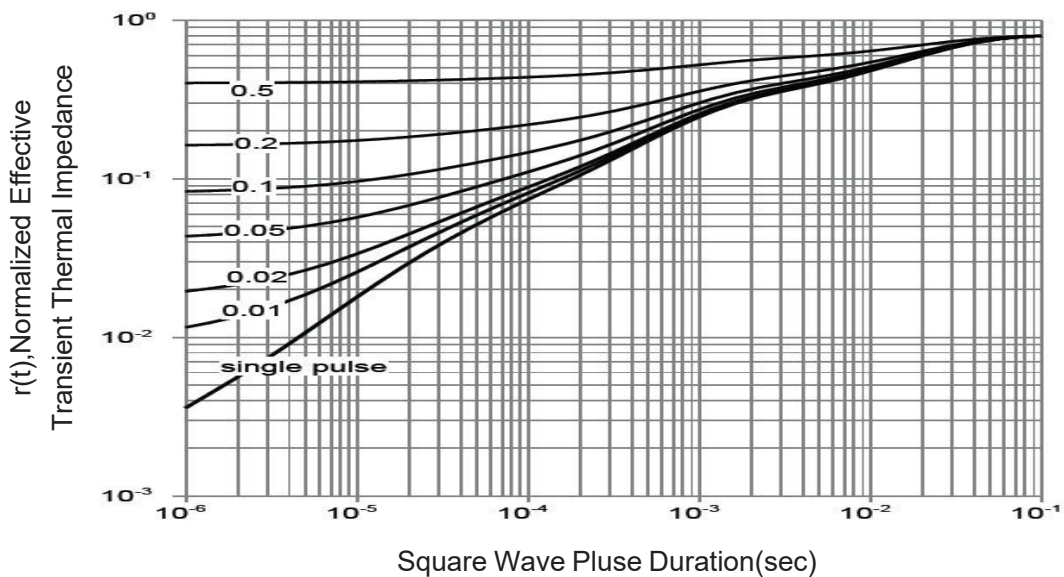


Figure 11 Normalized Maximum Transient Thermal Impedance